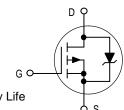
Product Preview

Medium Power Surface Mount Products

TMOS Single P-Channel Field Effect Transistors

WaveFET™ devices are an advanced series of power MOSFETs which utilize Motorola's High Cell Density HDTMOS process. These miniature surface mount MOSFETs feature ultra low RDS(on) and true logic level performance. They are capable of withstanding high energy in the avalanche and commutation modes and the drain—to—source diode has a very low reverse recovery time. WaveFET™ devices are designed for use in low voltage, high speed switching applications where power efficiency is important. Typical applications are dc—dc converters, and power management in portable and battery powered products such as computers, printers, cellular and cordless phones. They can also be used for low voltage motor controls in mass storage products such as disk drives and tape drives. The avalanche energy is specified to eliminate the guesswork in designs where inductive loads are switched and offer additional safety margin against unexpected voltage transients.



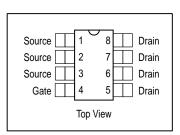
- Ultra Low RDS(on) Provides Higher Efficiency and Extends Battery Life
- Logic Level Gate Drive Can Be Driven by Logic ICs
- Miniature SO–8 Surface Mount Package Saves Board Space
- Diode Is Characterized for Use In Bridge Circuits
- Diode Exhibits High Speed, With Soft Recovery
- IDSS Specified at Elevated Temperature
- Avalanche Energy Specified
- Mounting Information for SO-8 Package Provided

MMSF3305

Motorola Preferred Device

SINGLE TMOS
POWER MOSFET
9.1 AMPERES
30 VOLTS
RDS(on) = 0.02 OHM





DEVICE MARKING

ORDERING INFORMATION

S3305	Device	Reel Size	Tape Width	Quantity
33303	MMSF3305R2	13″	12 mm embossed tape	4000 units

Preferred devices are Motorola recommended choices for future use and best overall value.

This document contains information on a product under development. Motorola reserves the right to change or discontinue this product without notice.

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MMSF3305

	Rating	Symbol	Max	Unit
Drain-to-Source Voltage		VDSS	30	V
Drain-to-Gate Voltage (RGS = 1.0 l	ΜΩ)	VDGR	20	V
Gate-to-Source Voltage — Continu	ous	VGS	± 20	V
1 inch SQ. FR-4 or G-10 PCB 10 seconds	Thermal Resistance — Junction to Ambient Total Power Dissipation @ T _A = 25°C Linear Derating Factor Drain Current — Continuous @ T _A = 25°C Continuous @ T _A = 70°C Pulsed Drain Current (1)	RTHJA PD I _D	50 2.5 20 9.1 7.3	°C/W Watts mW/°C A A
Minimum FR-4 or G-10 PCB	Thermal Resistance — Junction to Ambient Total Power Dissipation @ T _A = 25°C Linear Derating Factor	RTHJA PD	50 80 1.56 12.5	°C/W Watts mW/°C
10 seconds	Drain Current — Continuous @ T _A = 25°C Continuous @ T _A = 70°C Pulsed Drain Current (1)	I _{DM}	7.2 5.8 40	A A A
Operating and Storage Temperature Range		TJ, T _{stg}	- 55 to 150	°C
Single Pulse Drain-to-Source Avala (V _{DD} = 30 Vdc, V _{GS} = 10 Vdc, Poly No. 10 Vdc, Poly N	anche Energy — Starting T_J = 25°C eak I_L = 9.1 Apk, L = TBD mH, R_G = 25 Ω)	EAS	TBD	mJ

⁽¹⁾ Repetitive rating; pulse width limited by maximum junction temperature.

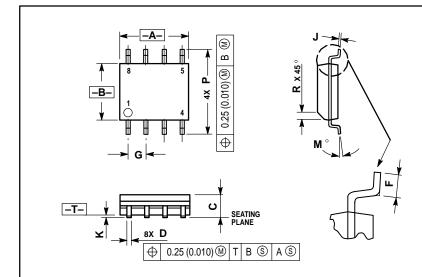
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS					•	•	•
Drain-to-Source Breakdown Voltage (1) (3) (VGS = 0 Vdc, ID = 0.25 mAdc) Temperature Coefficient (Positive)		V _{(BR)DSS}	30 —	_ _	_ _	Vdc mV/°C	
Zero Gate Voltage Drain Current (V _{DS} = 30 Vdc, V _{GS} = 0 Vdc) (V _{DS} = 15 Vdc, V _{GS} = 0 Vdc, T _J = 70°C)		IDSS	_	_ _	1.0 5.0	μAdc	
Gate–Body Leakage Current (V _{GS} = ± 20 Vdc, V _{DS} = 0)			IGSS	_	_	100	nAdc
ON CHARACTERISTICS ⁽¹⁾							•
Gate Threshold Voltage (V _{DS} = V _{GS} , I _D = 0.25 mAdc) Threshold Temperature Coefficient (Ne	egative)	(1) (3)	VGS(th)	0.7	_	1.4 —	Vdc mV/°C
Static Drain-to-Source On-Resistance (VGS = 10 Vdc, I_D = 9.1 Adc) (VGS = 4.5 Vdc, I_D = 7.3 Adc)		(1) (3)	R _{DS(on)}	_	_ _	20 30	mΩ
On–State Drain Current (V _{DS} ≤ 5.0 V, V _{GS} = 10 V) (V _{DS} ≤ 5.0 V, V _{GS} = 4.5 V)			I _{D(on)}	40 10	_ _	_ _	А
Forward Transconductance (V _{DS} = 15 V	'dc, I _D = 8.0 Adc)	(1)	9FS	_	_	_	Mhos
DYNAMIC CHARACTERISTICS							
Input Capacitance	0.4	- > / ·	C _{iss}	_	_	TBD	pF
Output Capacitance	$(V_{DS} = 30 \text{ Vdc}, V_{GS} = 0 \text{ Vdc}, f = 1.0 \text{ MHz})$		C _{oss}	_	_	TBD	
Transfer Capacitance			C _{rss}	_	_	TBD	
SWITCHING CHARACTERISTICS(2)							•
Turn-On Delay Time			^t d(on)	_	_	TBD	ns
Rise Time	$(V_{DD} = 15 \text{ Vdc}, I_{D} = 1.0 \text{ Adc}, V_{GS} = 10 \text{ Vdc}, R_{G} = 6.0 \Omega)$ (1)		t _r	_	_	TBD	
Turn-Off Delay Time			^t d(off)	_	_	TBD	
Fall Time			t _f	_	_	TBD	
Gate Charge			QT	_	_	TBD	nC
See Figure 8	$(V_{DS} = 15 \text{ Vdc}, I_D = 4.6 \text{ Adc}, V_{GS} = 10 \text{ Vdc}) (1)$		Q ₁	_	_	_	
			Q ₂	_	_	_	
			Q ₃	_	_	_	
SOURCE-DRAIN DIODE CHARACTERIS	STICS						
Forward On–Voltage ⁽¹⁾	(I _S = 2.1 Adc, V _{GS} = S = 2.1 Adc, V _{GS} = 0 V _G	= 0 Vdc) (1) dc, T _J = 125°C)	V _{SD}	_		1.2 —	Vdc
Reverse Recovery Time	(I _S = 2.1 Adc, V _{GS} = 0 Vdc, dI _S /dt = 100 A/μs) (1)		t _{rr}	_	_	TBD	ns
See Figure 15			t _a	_	_	_	
			t _b	_	_	_	
Reverse Recovery Stored Charge			Q _{RR}	_	_	_	μС

(1) Pulse Test: Pulse Width
$$\leq$$
 300 μ s, Duty Cycle \leq 2%.
(2) Switching characteristics are independent of operating junction temperature.
(3) Reflects typical values.
$$C_{pk} = \left| \frac{\text{Max limit} - \text{Typ}}{3 \text{ x SIGMA}} \right|$$

(4) Repetitive rating; pulse width limited by maximum junction temperature.

PACKAGE DIMENSIONS



CASE 751-05 SO-8 ISSUE P

- 1. DIMENSIONS A AND B ARE DATUMS AND T IS A DATUM SURFACE.
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- DIMENSIONS ARE IN MILLIMETER.
 DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.

 MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- DIMENSION D DOES NOT INCLUDE MOLD PROTRUSION, ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.80	5.00	
В	3.80	4.00	
С	1.35	1.75	
D	0.35	0.49	
F	0.40	1.25	
G	1.27 BSC		
J	0.18	0.25	
K	0.10	0.25	
М	0°	7°	
Р	5.80	6.20	
R	0.25	0.50	

STYLE 13:

PIN 1. SOURCE

- SOURCE 2.
- 3. SOURCE
- GATE DRAIN
- 5
- DRAIN 6. DRAIN
- 8. DRAIN

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